



# **Ultrahigh-Speed Switching Applications**

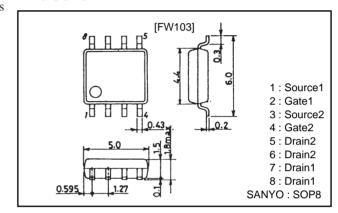
### **Features**

- Low ON resistance
- Ultrahigh-speed switching.
- Composite type with two 4V-drive P-channel MOSFETs facilitating high-density mounting.
- Matched pair capability.

### **Package Dimensions**

unit: mm

### 2129-SOP8



## **Specifications**

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-3	Α
Drain Current (pulse)	IDP	PW≤10µs, duty cycle≤1%	-32	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (1000mm <sup>2</sup> ×0.8mm) 1unit	1.7	W
Total Dissipation	PT	Mounted on a ceramic board (1000mm <sup>2</sup> ×0.8mm)	2.0	W
Channel Temperature	Tch		150	°C
Storage temperature	Tstg		-55 to +150	°C

### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
D-S Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0	-30			V
Zero-Gate-Voltage Drain Current	IDSS	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0			-100	μA
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.0		-2.5	V
Forward Transfer Admittance	ly <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-3A	2	4		S
Static Drain-to-Source	R <sub>DS(on)</sub>	I <sub>D</sub> =-3A, V <sub>G</sub> S=-10V		95	125	mΩ
ON-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =-3A, V <sub>G</sub> S=-4V		150	205	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, f=1MHz		550		pF
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		370		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =-10V, f=1MHz		70		pF

Continued on next page.

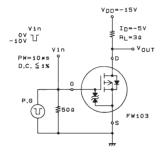
Continued from preceding page.

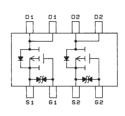
Parameter	Symbol	Conditions	Ratings			- Unit
	Symbol		min	typ	max	O'III
Turn-ON Delay Time	td(on)	See specified Test Circuit.		20		ns
Rise Time	t <sub>r</sub>	"		110		ns
Turn-OFF Delay Time	td(off)	"		330		ns
Fall Time	tf	"		170		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-3A, V <sub>GS</sub> =0		-1.0	-1.2	V

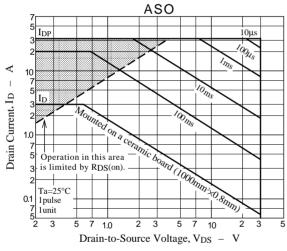
# **Switching Time Test Circuit**

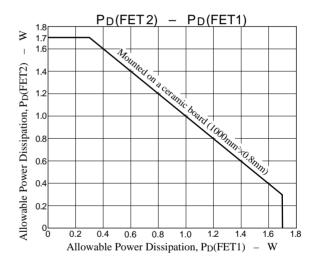
### **Electrical Connection**

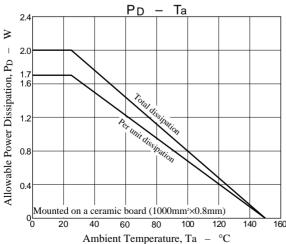
(Top view)











- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property lose.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
  - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use:
  - ② Not impose any responsibilty for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

This catalog provides information as of October, 1997. Specifications and information herein are subject to change without notice.